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YIELD MODELING FOR PHOTOLITHOGRAPHY

by

Chris A. Mack and Edward W. Charrier

FINLE Technologies, Inc.,
Austin, Texas

Chris A. Mack received bachelor of Science degrees in Physics, Chemistry, Electrical Engineering and Chemical Engineering from Rose-Hulman Institute of Technology in 1982 and a Master of Science degree in Electrical Engineering from the University of Maryland in 1989. He joined the Microelectronics Research Laboratory of the Department of Defense in 1983 and began work in optical lithography research. He has authored numerous papers in the area of optical lithography, regularly teaches courses on this topic, and has developed the lithography simulation programs PROLITH and PROLITH/2. During 1990-1991 he was on assignment at SEMATECH working in deep-UV photoresist characterization and phase-shifting mask optimization. Since January of 1992 he has been with FINLE Technologies where he now serves as President and Chief Technical Officer. Mr. Mack is also an adjunct faculty at The University of Texas at Austin. His current interests are in advanced techniques for ultrafine lithography and the application of lithography simulation to research, development and manufacturing.

Edward W. Charrier received a B.S.E. in Mechanical Engineering from The University of Michigan in 1985 and an M.B.A. from The University of Texas at Austin in 1993. He founded Laboratoty Integration Systems, Inc., a company specializing in PC data acquisition systems for research laboratories, and has developed numerous software products for research and information management applications. He joined FINLE Technologies in February of 1994 as Director of Marketing and Business Development.

ABSTRACT

A method is presented for predicting the CD limited yield of a photolithographic process using well established lithography modeling tools. The lithography simulator PROLITH/2 is used to generate a multi-variable process response space (for example, final resist critical dimension (CD) versus focus, exposure, resist thickness, etc.). Error distributions are then determined for each input variable; for example, normal distributions may be assumed. By correlating the input error distribution with the process response space, a final CD distribution is generated. Analysis of the output distribution can produce a predicted parametric CD yield. Further, this methodology, can be used to optimize the process to maximize the yield.

INTRODUCTION

Predicting the yield of a lithographic process is difficult to the point that it is rarely attempted. For example, Cost of Ownership (COO) modeling and other cost methods for making decisions in lithography lack an accurate method for determining the parametric yield of a lithography step. As a result, most COO efforts simply assume a value for yield (e.g., 97%) and never change the value. Further, if yield could be predicted in a quantitative manor, the method for predicting yield could be used to optimize yield as well. Is a process which gives the nominal critical dimension (CD) at the nominal values for all inputs the same process which gives the maximum yield?

It is possible to accurately predict the parametric CD yield of a photolithographic process using well established lithography modeling tools. In this paper we will introduce a simple three step process for predicting CD yield. First, using the lithography simulator PROLITH/2, a multi-variable process response space is generated (for example, final resist critical dimension (CD) versus focus, exposure, resist thickness, etc.). Second, error distributions are determined for each input variable. For example, normal distributions may be assumed or more complicated distributions may be used. Third, by correlating the input error distribution with the process response space, a final CD distribution is generated. Analysis of the output distribution produces a predicted parametric CD yield using some acceptance criterion for CD. This number can serve as a direct input to a COO modeling effort of the simulated process or equipment, or can be used to help optimize the yield of a given process.

THEORY

There is, of course, an extensive literature and experience base on error analysis that can be applied to the prediction of CD limited yield. A very typical approach to predicting an error in critical dimension (ΔCD) resulting from a number of input errors (Δxi) is the use of the total derivative.

$$\Delta CD = \frac{\partial CD}{\partial x_1}\Delta x_1 + \frac{\partial CD}{\partial x_2}\Delta x_2 + \frac{\partial CD}{\partial x_3}\Delta x_3 + \cdots \quad (1)$$

where each partial derivative represents the process response of CD to the input variable x_i. Equation (1) is exact in the limit of infinitely small input errors. As the errors become larger (i.e., realistic) equation (1) remains accurate so long as the process response remains linear over the range of the error (i.e., the partial derivatives remain constant). If, however, the process response is non-linear the use of the total derivative error equation can be both misleading and inaccurate.

If both the input error distribution and the process response are known, the assumption of linearity is not needed — the resulting CD output distribution can be calculated directly. While both the input errors and the processes response can be determined experimentally, process simulation offers the capability to predict the process response. Consider a simple example to illustrate the method — the effect of exposure errors on linewidth. The process response in this case is the well known exposure latitude curve. If the input error distribution is known, correlation of the input error probability with the process response function gives the output error distribution. For this example let us assume that the exposure errors are normally distributed about the mean with a 3σ of 10% (Figure 1). The error distribution is plotted as the frequency of occurrence (or probability of occurrence) versus exposure energy with arbitrary units for frequency. The process response is linewidth versus exposure energy and in this case was predicted using the lithography simulation program PROLITH/2. The parameters for the simulation are given in Table I. For any given exposure energy, there is a probability that this energy will occur (for example, 200 mJ/cm^2 has a probability of 0.021 in Figure 1). From the process response curve, an exposure energy corresponds to a specific CD (for example, 0.513 µm for an energy of 200 mJ/cm^2) and thus must have the probability of occurrence corresponding to the probability of the exposure energy. Correlation of the input error distribution with the process response results in a list of linewidth values with corresponding frequencies of occurrence. The linewidth can then be divided up into equal size bins (for Figure 1, the bin size is 0.004 µm) and all of the probabilities with CDs within a given bin are summed. The result is plotted as a histogram of frequency versus CD and represents the resulting output CD error distribution.

The procedure described above and illustrated in Figure 1 is not limited to one input error variable. Multiple simultaneous variations in input parameters can be modeled to produce a full process response space. Individual input error functions can be combined by multiplying the individual probabilities to create a single multi-dimensional probability function. The assumption here is that the input errors are independent. The multi-dimensional error function and the multi-dimensional process response are then mapped to the standard one-dimensional output distribution.

Once a CD distribution has been predicted, the calculation of CD limited yield used here is straightforward. Given some CD specification (for example, the mean ±(10%), the frequencies of all CDs within spec are summed and divided by the sum of the frequencies for all CDs to give the yield. There are several subtle assumptions built into this approach, depending on the interpretation of the input error distribution and the impact of an out-of-spec linewidth. If the input error distribution is a die-to-die variation in the variable, then a CD out of spec means that CDs over the entire die are out of spec, resulting in a failed die. If the input error distribution is an error across one die, then the output is the CD distribution across a die. Yield loss would then depend on the specifics of the die. For example, yield loss may result if even one CD is beyond some specification, or it could result if some number of CDs are beyond some other specification, or both. Given an understanding of how CD errors cause device failures, a suitable prediction of yield from a known CD distribution can be accomplished. If both across the die and die-to-die errors must be considered, two separate (though coupled) yields may be necessary. For the purposes of this paper, the simple yield calculation described first will be used. It should also be noted that a feature may "fail" because of other attributes besides CD. For example, the photoresist sidewall angle may have a specification which could result in a failure. The modeling approach presented here could easily be extended to include sidewall angle and other metrics of lithographic quality.

RESULTS

Several examples of the use of the methodology described in this paper are presented here. First, two examples of using one-dimensional responses are shown for exposure dose and resist thickness inputs. Second, a two dimensional case in which both exposure and resist thickness vary simultaneously is presented. Finally, four inputs are allowed to vary to illustrate the extension to more realistic process conditions.

1-D Inputs

Figure 1 illustrates the simplest example of one error input. Although the calculations are straightforward, the results nonetheless revealing. Notice that the normal input error distribution does not result in a normal output distribution. Because the process in non-linear, the output distribution is slightly skewed (the probability of getting a +0.02 µm CD error is higher than the probability of a –0.02 µm error). Although in this case the exposure response is only slightly non-linear over the ±10% exposure range, it is sufficient to show the effect. Also notice that since the process response in monotonic, the CD with the highest probability of occurrence corresponds to the exposure dose with the highest probability of occurrence.

A second more interesting example of a single input error is resist thickness. The response of the linewidth to changes in resist thickness (called a swing curve) is not only highly non-linear, it is not monotonic. Figure 2 shows swing curves simulated with PROLITH/2 for resist exposure on polysilicon both with and without a top layer antireflection coating (TAR). Because of the sinusoidal nature of the response, the resulting CD distribution is very sensitive to both the mean and the 3σ of the input error. Figure 3 shows various output CD distributions for various input errors using the swing curve without TAR as the process response. Figure 3a shows the result where the nominal resist thickness is set at a maximum of the swing curve and the error is assumed to be normal with a 3σ width of 0.06µm, corresponding to half of one swing period. As one would expect, the CD distribution is highly skewed. All resist thickness errors result in smaller than nominal CDs. Operation at a minimum of the swing curve results in a similar, though reversed, skewed distribution (Figure 3b). In both cases, the *mean* of the CD distribution is not the CD at the minimum or maximum of the swing curve.

Figure 3c shows the case where the nominal resist thickness is set halfway between a minimum and a maximum of the swing curve. Even though the input error is normally distributed, the nonmonotonic nature of the process response results in a bimodal output distribution. In fact, the CD which corresponds to the most probable resist thickness is one of the least probable CD results. A similar result occurs whenever the resist thickness errors include an appreciable amount of both a minimum and a maximum of the swing. In Figure 3d, the mean resist thickness is set at a maximum but the 3σ width is one full period. The result again is a bimodal CD distribution, though skewed this time. Finally, in Figure 3e the CD distribution is tightened considerably when the resist thickness distribution is tightened to one-quarter of one swing period.

Figure 4 compares the distributions resulting from swing curves with and without TAR. In both cases the nominal resist thickness was set at a maximum of the swing and the 3σ error was 0.06μm (half of a period). As expected, the use of a top layer antireflection coating, which significantly reduces the swing curve amplitude, will significantly improve the resulting CD distribution.

2-D Input

The above examples showed two one-dimensional input variable cases. But what if resist thickness and exposure energy were varying independently, but at the same time? For such a case, the 1-D analysis method can be easily extended to two dimensions. If the two input errors are independent (as is usually the case), their individual 1-D probability functions can be multiplied together to obtain a 2-D probability function. Figure 5 shows such a 2-D input error function assuming both exposure energy and resist thickness errors are normally distributed. The PROLITH/2 lithography simulator was used to map out the entire two dimensional process response space, which is also shown in Figure 5. Note that the two dimensional response is not the product of the two one dimensional responses. Careful examination of Figure 5 shows that the swing curve amplitude decreases with increasing exposure dose showing that the two variables are coupled in their impact on CD. The calculation of the CD distribution is carried out in the same manner as in the 1-D case using a mean exposure energy as the nominal dose to size with a 3σ of 10%, and a mean resist thickness set at a maximum of the swing curve with a 3σ of half a period.

Looking at the result (Figure 5), the distribution is skewed due to the swing curve, but is somewhat smoothed out due to the exposure errors. One extremely important result is that the mean of the CD distribution is not the nominal CD, even though the nominal CD would occur for the mean of the exposure and resist thickness distributions. The reason for this is the non-linear nature of the process response.

4-D Input

Finally, to show the application of this methodology to more complicated (and more realistic) situations, four input variables were used: focus, exposure energy, resist thickness, and the development parameter R_{max}. The meaning of the first three terms are self-evident and R_{max} is the aximum development rate of the photoresist corresponding to completely exposed positive resist. Changing R_{max} scales the development rate and could be used to account for a variety of process variations which affect photoresist development properties. PROLITH/2 was used to simulate the 4-D process response space centered around the baseline process of Table I. Using the nominal process as the center of the 4-D error function with 3σ values given in Table II, the CD distribution was calculated and is shown in Figure 6a. The shape is characteristic of the skew caused by the swing curve, but spread out considerably due to the other variables. The mean of the resulting CD distribution is 0.480 μm with a calculated yield of 87.7% based on a ±10% CD specification. The below nominal mean linewidth indicates that the nominal process is not "centered" despite that non-statistical evidence to the contrary.

Since the mean linewidth of the nominal process is undersized by 4%, could shifting the process result in an improvement in yield? Such a question can be easily answered. The most difficult part of the yield calculation is the calculation of the process response space, which is independent of the error input functions. The errors can be easily manipulated and a new yield calculated using the already calculated process response space. To find the process which optimizes the CD limited yield, the mean of each of the four input errors was varied, keeping the 3σ values constant. Yield was calculated for each process condition. The best result, shown in Figure 6b, used the same process as the nominal but with the exposure energy reduced by about 8%. This "under-exposure" shifted the mean linewidth up to the nominal linewidth and resulted in a significant increase in yield (to 94.8%).

CONCLUSIONS

Several important conclusions can be drawn from this work. First, lithography simulation tools can be used to conveniently calculate large, multi-dimensional process response spaces. Second, a knowledge of the error distribution for each input variable can be combined with the process response to give a predicted CD distribution at the output. This distribution can be further analyzed to give a single yield number to characterize the quality of the process. With such a method for predicting linewidth distributions and CD limited yield, many applications are possible. Different processes can be compared using yield as the metric, both for use in Cost of Ownership models and for process optimization studies.

There are many opportunities for future work. First, in this paper, only normal input errors were used. This limitation is not necessary and was only imposed for convenience. Any arbitrary input error distribution can be used. Second, other process parameters can be investigated either alone or in combination with the parameters used in this paper. Third, other outputs can be used. For example, yield could be defined based on a combination of CD, resist sidewall angle, and resist thinning. Fourth, other feature types and sizes can be simulated. A plot of CD limited yield versus feature size can be generated which would be of great value in predicting the application of current processes to smaller features and for identifying specific goals for improving a process for use in some future device generation.

Parameter	Value
Projection System:	
Nominal linewidth	0.50 μm
Pitch	1.00 μm
Wavelength	365 nm
Numerical aperture	0.54
Image reduction ratio	5:1
Partial coherence	0.5
Focal position	-0.3 μm
Nominal exposure dose	210 mJ/cm^2
Substrate	Silicon
Layer 1	Oxide, 30 nm
Layer 2	Polysilicon, 350 nm
Post-Exposure Bake:	
PEB diffusion length	60 nm
Development:	
Time	60 seconds
Maximum development rate	150 nm/s
Minimum development rate	0.05 nm/s
Threshold PAC concentration	-100
Selectivity	6.0
Resist System:	
Thickness	1.04 μm
Parameter A	0.800 μm^{-1}
Parameter B	0.300 μm^{-1}
Parameter C	0.016 cm^2/mJ
Index of refraction	1.75

Table I: PROLITH/2 lithography simulation parameters used as a baseline for the simulations in this study.

Parameter	Mean	3σ
Exposure energy	210 mJ/cm^2	21 mJ/cm^2
Resist thickness	1.04 μm	0.06 μm
Focus	-0.3 μm	0.5 μm
Development R_{max}	150 nm/s	30 nm/s

Table II: Input error distributions for the nominal process of the four-dimensional test case.

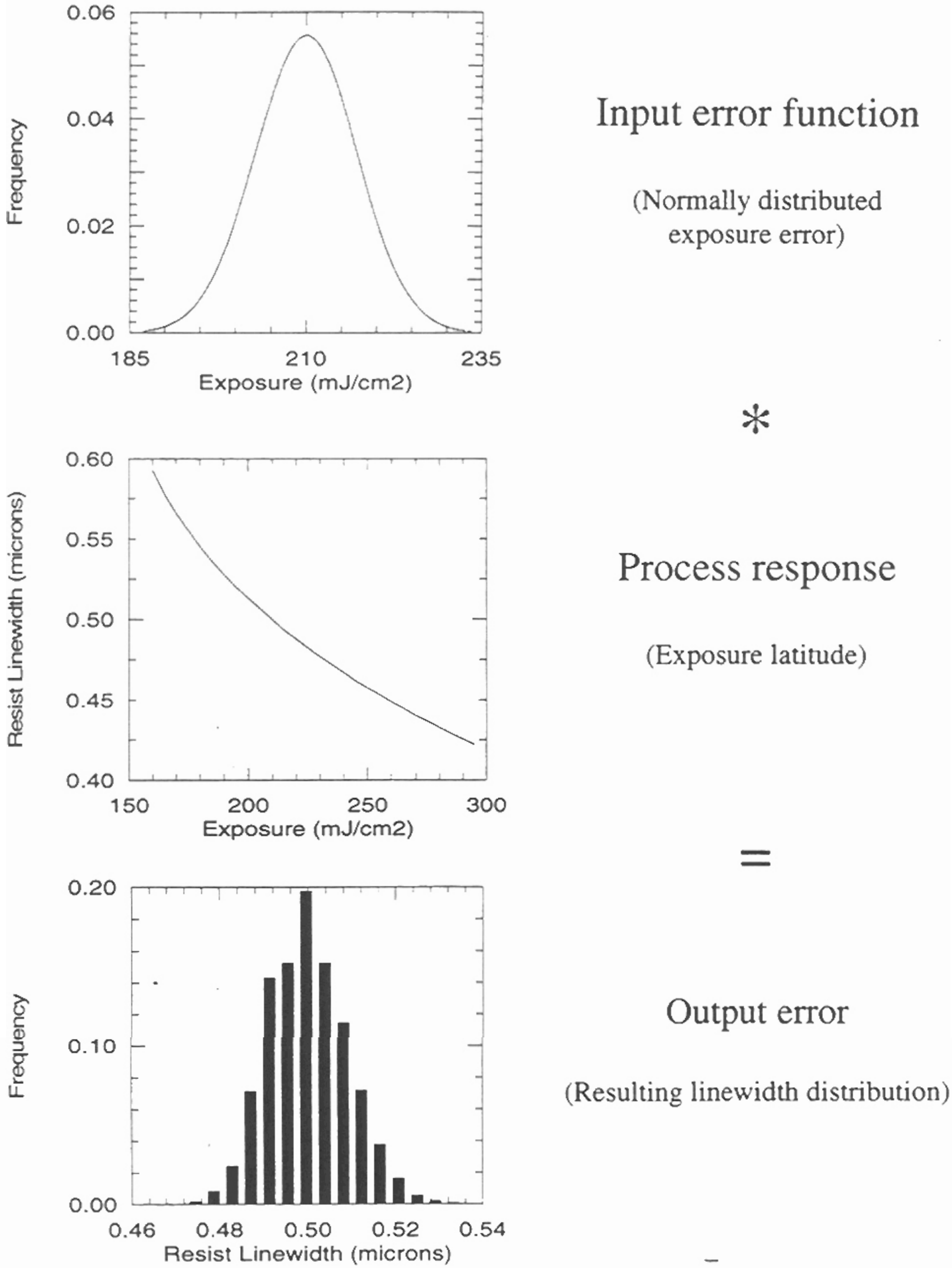

Figure 1: Example of an output error distribution from a normal input error function and a simulated process response for the one-dimensional case.

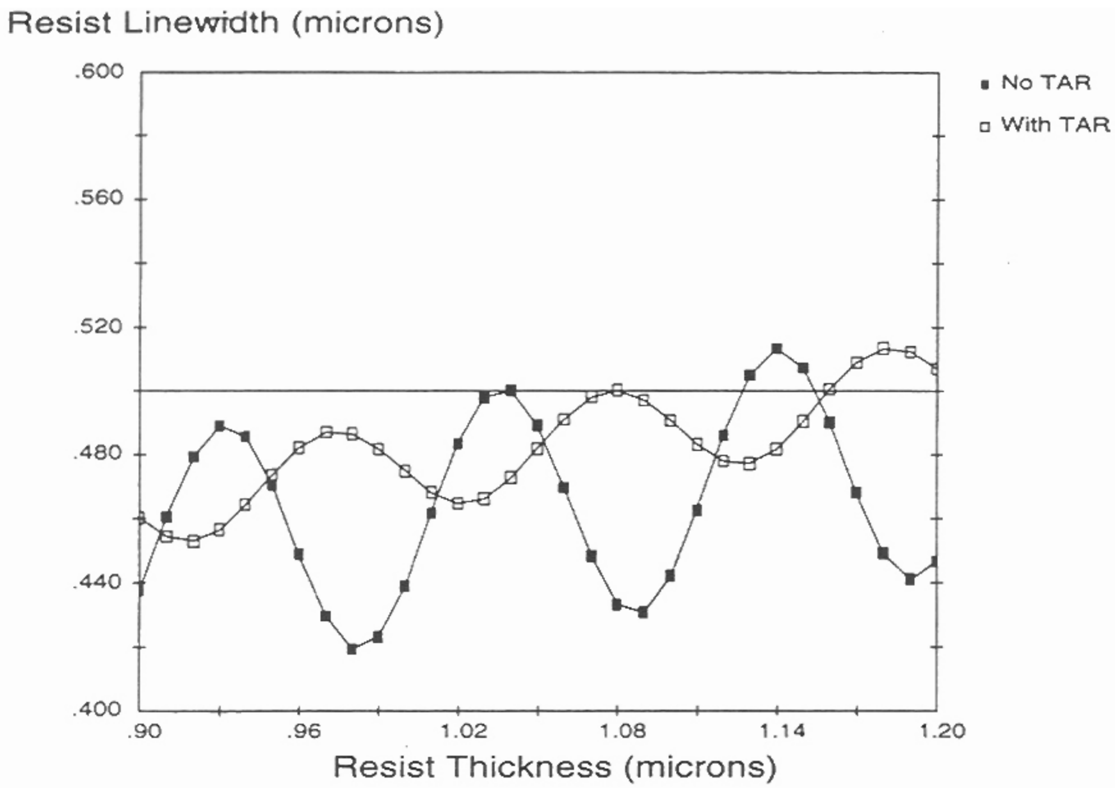

Figure 2: Swing curves from a PROLITH/2 simulation for cases with and without TAR.

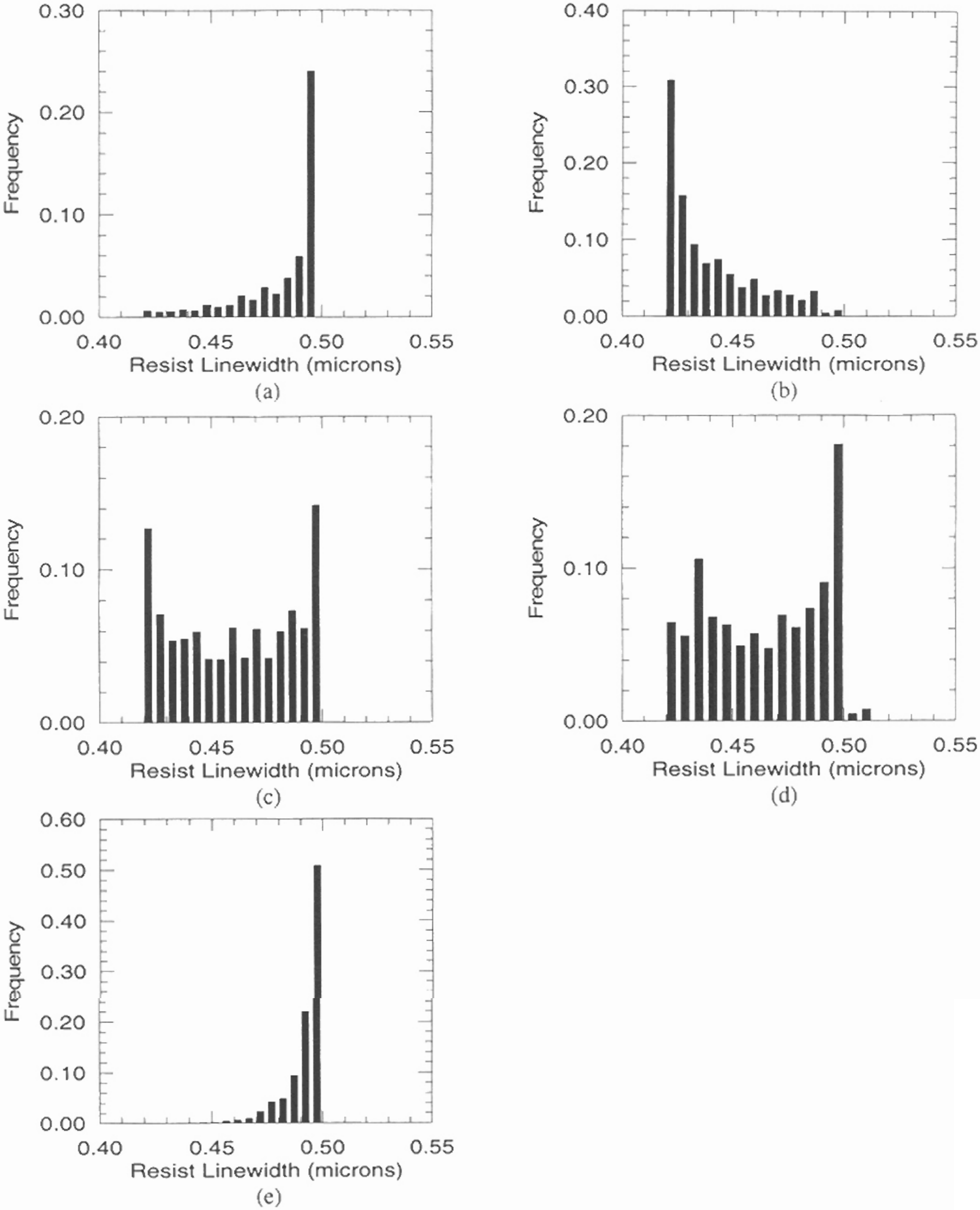

Figure 3: Linewidth distribution from a swing curve (without TAR) with resist thickness error functions of: (a) Mean at maximum (1.04 μm), 3σ = 1/2 period of swing (0.06 μm); (b) Mean at minimum (0.98 μm), 3σ = 1/2 period of swing (0.06 μm); (c) Mean centered between a maximum and a minimum (1.01 μm), 3σ = 1/2 period of swing (0.06 μm); (d) Mean at maximum (1.04 μm), 3σ = period of one swing (0.12 μm); (e) Mean at maximum (1.04 μm), 3σ = 1/4 period of swing (0.03 μm).

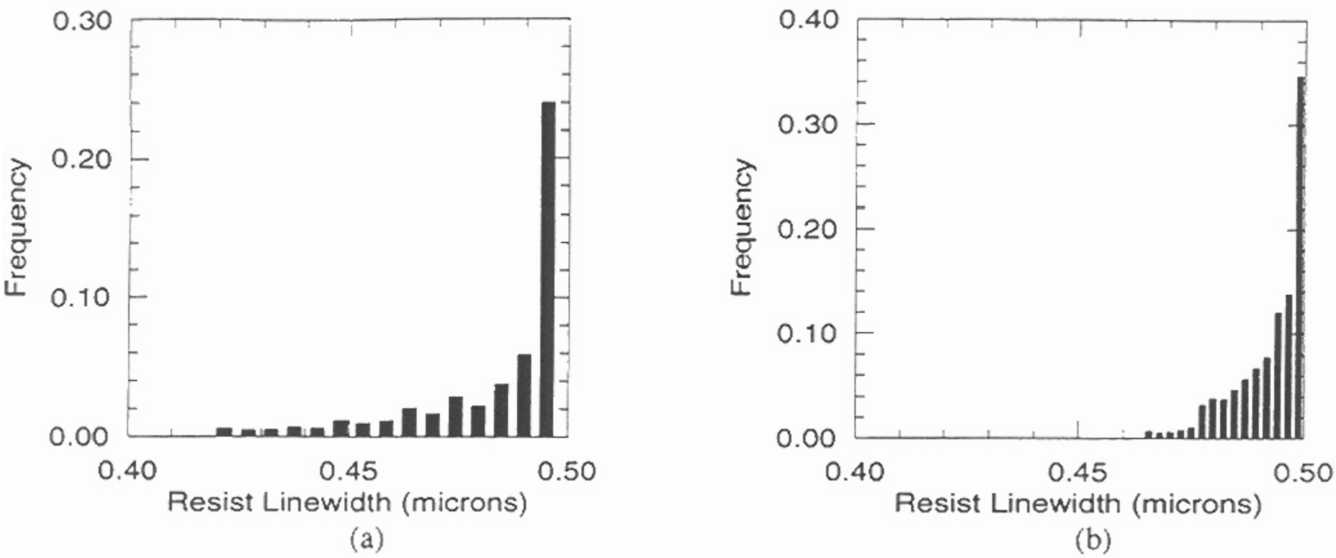

Figure 4: Linewidth distribution with resist thickness error functions of: mean at maximum, $3\sigma = 1/2$ period of swing for (a) swing curve without TAR and (b) swing curve with TAR.

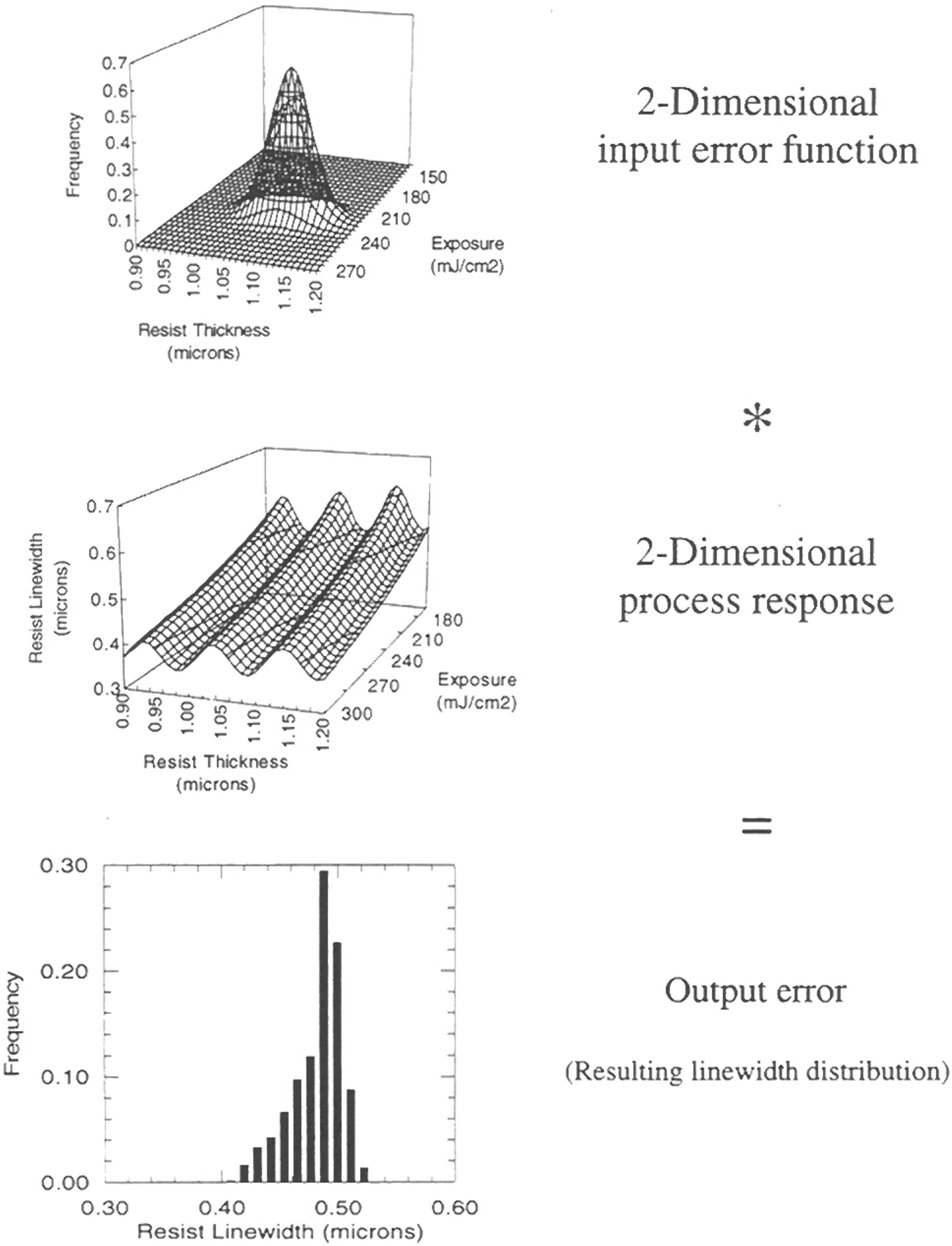

Figure 5: Example of an output error distribution from a normal input error function and a simulated process response for the two-dimensional case.

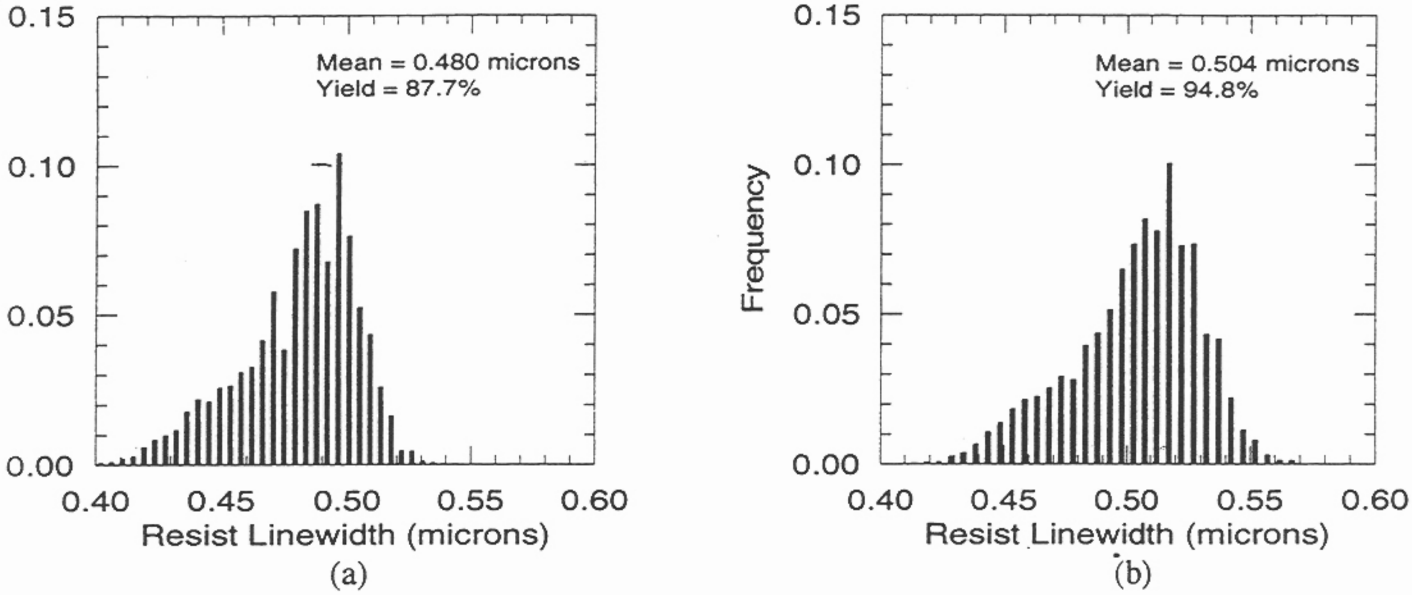

Figure 6: Linewidth distribution for the four input variable case: mean resist thickness at a maximum, mean focus at nominal, mean developer at nominal and (a) mean exposure at nominal (210 mJ/cm^2) and (b) mean exposure at 8.1% below nominal (193 mJ/cm^2) with yield based on CD specification of nominal ± 10%.